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Supporting information

High-conductive Cu-substituted brownmillerite with emergent 3-dimensional oxygen vacancy channels

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Figure S1. Surface topography of as-deposited (a) BM-SCO, (b) Cu10, (c) Cu20, (d) Cu33 and (e) Cu50.



Figure S2. The fast Fourier transform (FFT) of the STEM images in Figure 2a-j.



Figure S3. The d_{Sr-Sr} for (a) Cu10 and (b) Cu20 along in-plane and out-of-plane direction.



Figure S4. Cross-section of the Cu20 with both in-plane and out-of-plane arrangement of octahedra and tetrahedra layers.



Figure S5. Cross-section of (010) plane of Cu33.



Figure S6. (a) Atomic structure for the novel $3D^{V_0^{\bullet\bullet}}$ structure of Cu33; (b) shows the magnified view of the structure, which is one-eighth the size of that in (a).



Figure S7. Electron energy-loss spectra (EELS) of the O *K*-edges for Cu-doped SCOs. The pink line presenting the data of BM-SCO was quoted from the work of B. Cui, et al.¹



Figure S8. θ -2 θ scans for Cu33 and Cu50 after annealing under (a) high oxygen and (b) water vapor pressure atmosphere for 1hr.



Figure S9. *M*-*T* curves of (a) Cu10, (b) Cu20, (c) Cu33, and (d) Cu50 with the magnetic field of 200 Oe; the corresponding *M*-*H* loops measured at 10 K are shown in (e), (f), (g), and (h), respectively.



Figure S10. EDS intensity of Co, Ti and Nb across the film/substrate interface.

References

1. B. Cui, P. Werner, T. Ma, X. Zhong, Z. Wang, J. M. Taylor, Y. Zhuang and S. S. P. Parkin, *Nat. Commun.*, 2018, **9**, 3055.